

al
end

15. The nitride semiconductor light emitting device of claim 13, wherein the n-type clad layer has a thickness between $0.5\ \mu\text{m}$ and $1.7\ \mu\text{m}$. --

REMARKS

The above changes are designed to remove multiple dependency to avoid the additional fee therefor and to incorporate by reference the priority document. Prompt and favorable action on the merits are respectfully requested.

Respectfully submitted,

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